

# **BCR3AS-12B**

# Triac

Low Power Use

(The product guaranteed maximum junction temperature of 150°C)

REJ03G0450-0300 Rev.3.00 Nov 30, 2007

#### **Features**

I<sub>T(RMS)</sub>: 3 A
 V<sub>DRM</sub>: 600 V

•  $I_{FGT I}$ ,  $I_{RGT I}$ ,  $I_{RGT III}$ : 15 mA

Non-Insulated Type

Planar Passivation Type

#### **Outline**

RENESAS Package code: PRSS0004ZA-A

(Package name: MP-3A)





1. T<sub>1</sub> Terminal

2. T<sub>2</sub> Terminal

3. Gate Terminal

4. T<sub>2</sub> Terminal

# **Applications**

Hybrid IC, solid state relay, switching mode power supply, light dimmer, electric fan, electric blanket, control of household equipment such as washing machine, and other general purpose control applications

### Warning

- 1. Refer to the recommended circuit values around the triac before using.
- 2. Be sure to exchange the specification before using. Otherwise, general triacs with the maximum junction temperature of 125°C will be supplied.

# **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
T didinotoi	Cymbol	12		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V	

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T(RMS)</sub>	3	А	Commercial frequency, sine full wave 360° conduction, Tc = 133°C <sup>Note3</sup>
Surge on-state current	I <sub>TSM</sub>	30	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	3.7	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	3	W	
Average gate power dissipation	$P_{G(AV)}$	0.3	W	
Peak gate voltage	$V_{GM}$	6	V	
Peak gate current	$I_{GM}$	0.3	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	0.26	g	Typical value

Notes: 1. Gate open.

# **Electrical Characteristics**

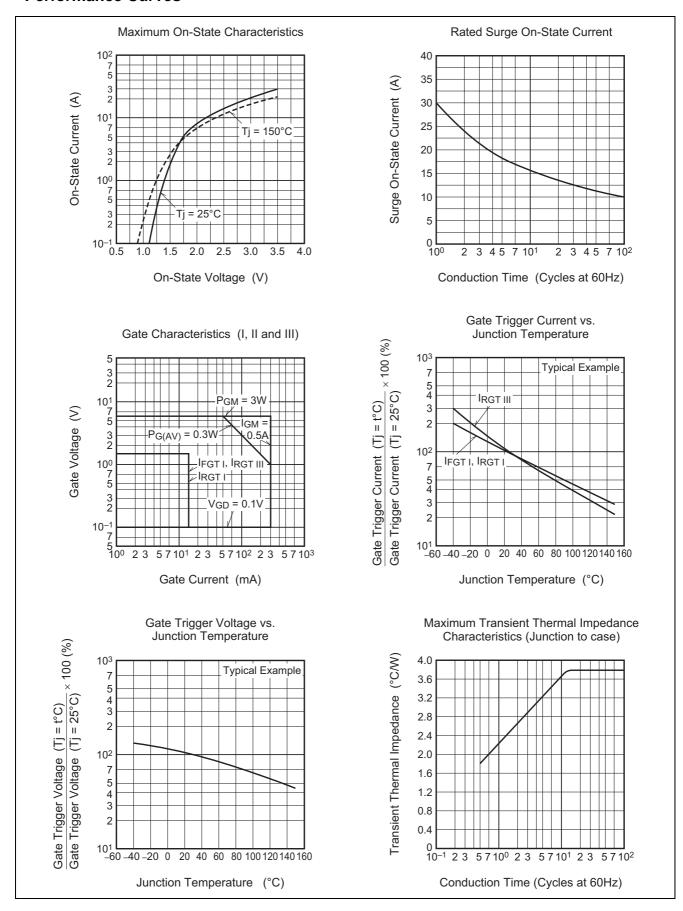
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0	mA	Tj = 150°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	1.7	V	$Tc = 25^{\circ}C$ , $I_{TM} = 4.5 A$ ,
							Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGT\ I}$	_	-	1.5	V	Tj = 25°C, $V_D$ = 6 V, $R_L$ = 6 Ω,
	II	$V_{RGT\; I}$	_		1.5	V	$R_G = 330 \Omega$
	III	$V_{RGT\;III}$	_	_	1.5	V	
Gate trigger current <sup>Note2</sup>	I	I <sub>FGT I</sub>	_		15	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ $\Omega$ ,
	II	I <sub>RGT I</sub>	_		15	mA	$R_G = 330 \Omega$
	III	I <sub>RGT III</sub>	_		15	mA	
Gate non-trigger voltage		$V_{GD}$	0.2/0.1	_	_	V	Tj = 125°C/150°C,
							$V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th(j-c)</sub>	_	_	3.8	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	5/1	_	_	V/μs	Tj = 125°C/150°C

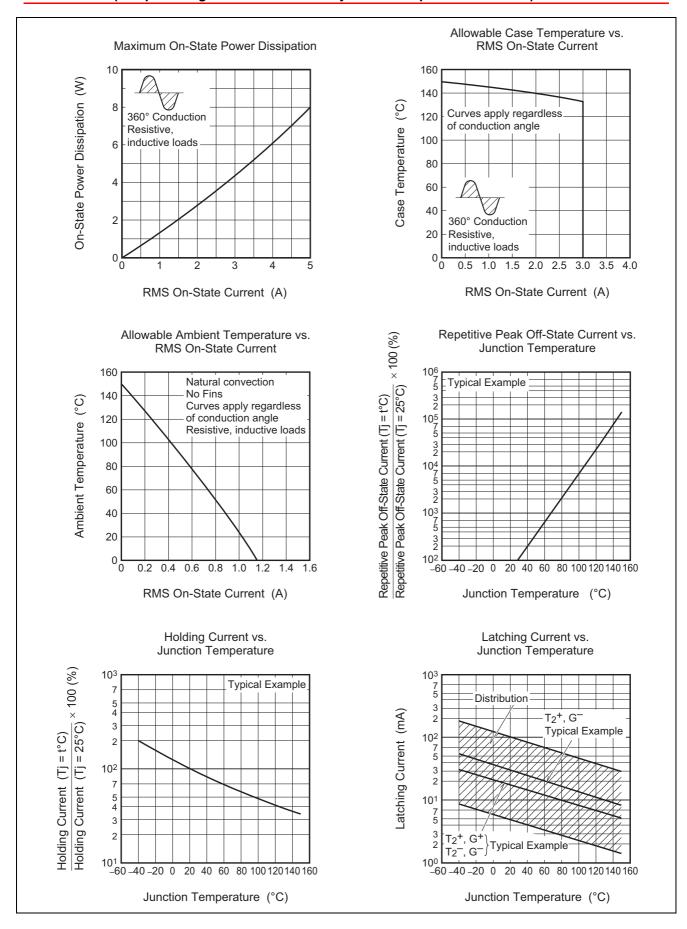
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

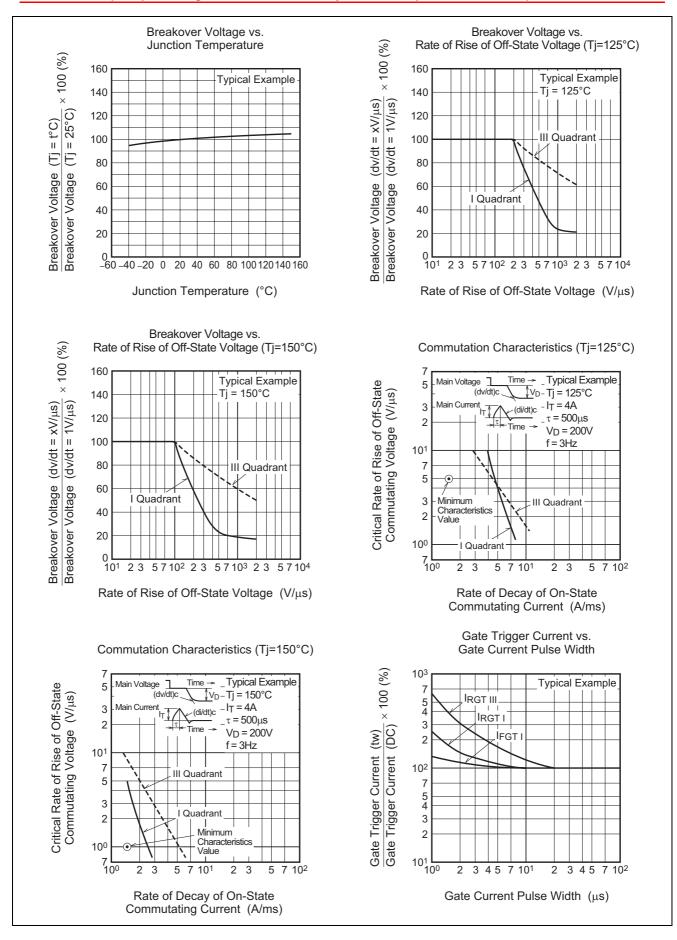
- 3. Case temperature is measured on the  $T_2$  tab.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C	Supply Voltage  → Time
<ul> <li>2. Rate of decay of on-state commutating current (di/dt)c = -1.5 A/ms</li> <li>3. Peak off-state voltage V<sub>D</sub> = 400 V</li> </ul>	Main Current  Main Voltage  (dv/dt)c  Time  (dv/dt)c

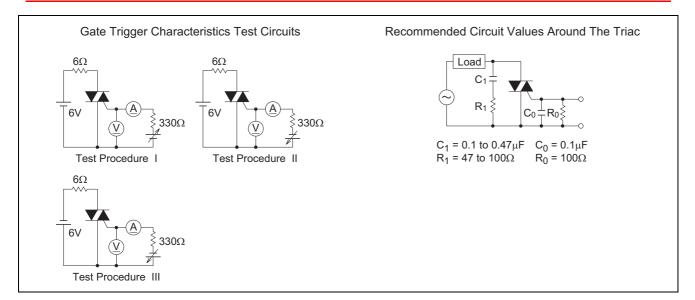
#### **Performance Curves**



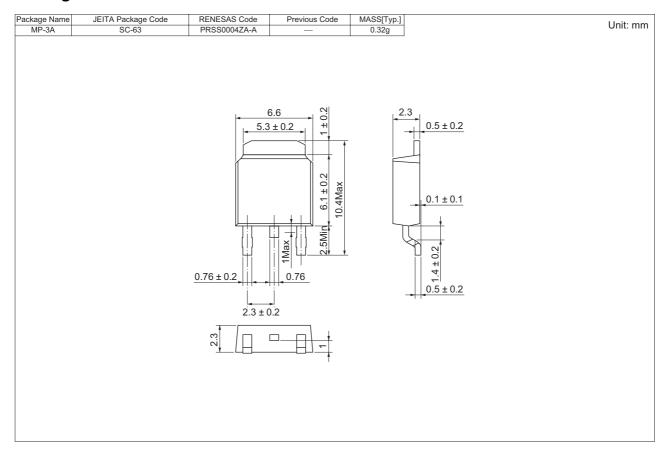




# BCR3AS-12B (The product guaranteed maximum junction temperature of 150°C)



# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	BCR3AS-12B-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	BCR3AS-12B

Note: Please confirm the specification about the shipping in detail.

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